

Supporting Information for:

Ambipolar Organic Phototransistors Based on 6,6'-Dibromoindigo

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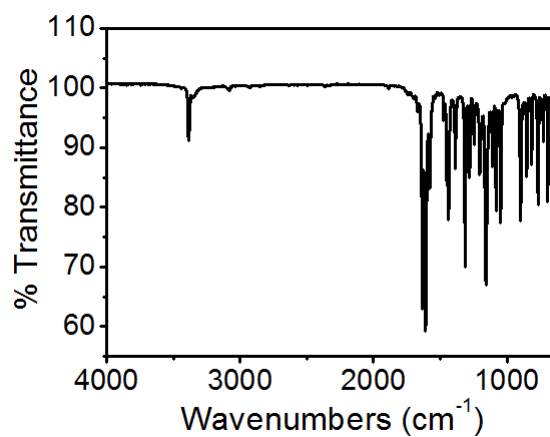


Figure S1. Infrared spectrum for 6-BrIG.

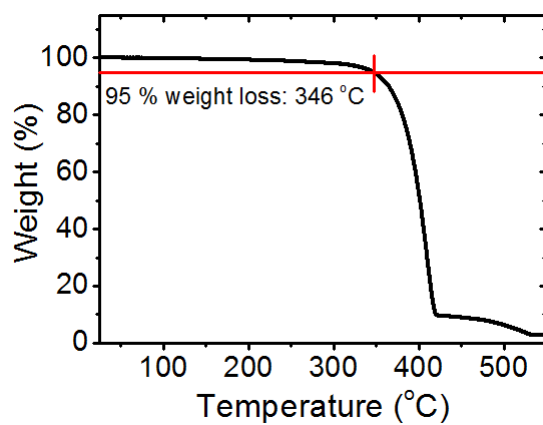


Figure S2. Thermogravimetric analysis of 6-BrIG.

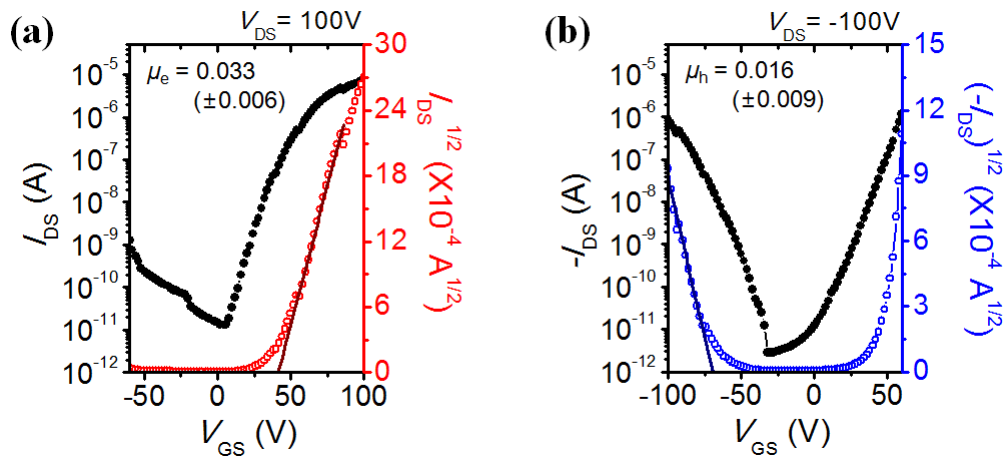


Figure S3. Current-voltage ($I_{DS} - V_{GS}$) characteristics measured in a N_2 -filled glovebox: (a) electron-enhancement operation, $V_{DS} = 100$ V and (b) hole-enhancement operation, $V_{DS} = -100$ V.

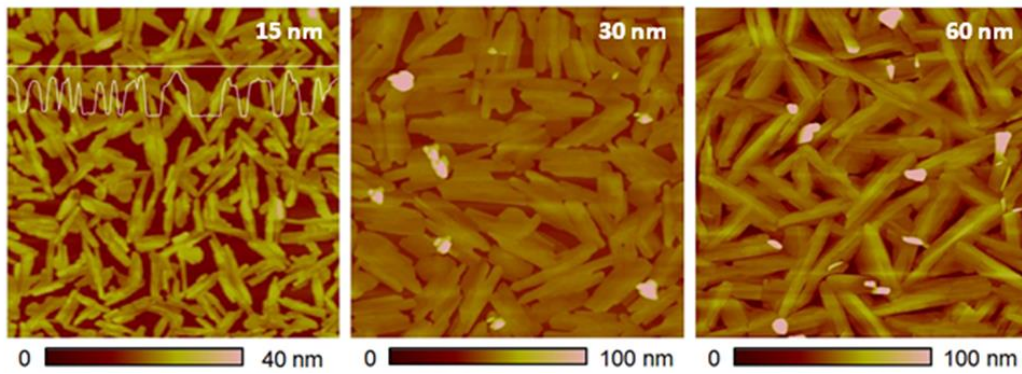


Figure S4. Tapping-mode AFM images ($5 \mu m \times 5 \mu m$) of 6-BrIG films with different film thickness on OTS-treated SiO_2/Si substrates annealed at $100^\circ C$.

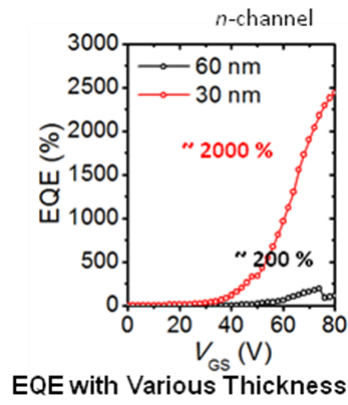


Figure S5. Comparison of the EQE values of 6-BrIG phototransistors with different film thicknesses.

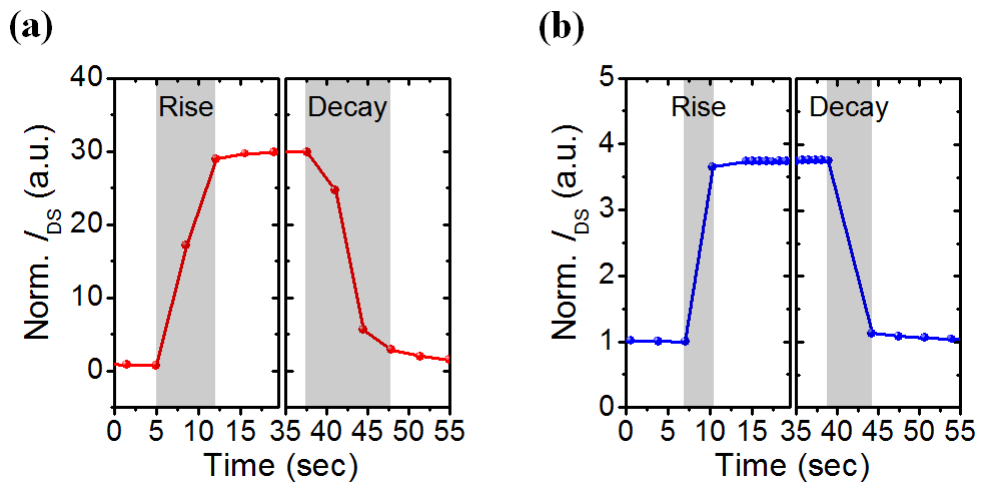


Figure S6. Switch-on and -off photocurrent responses as a function of time at $|V_{GS}| = 20$ V: (a) *n*-dominant operation applying $V_{DS} = 20$ V and (b) *p*-dominant operation applying $V_{DS} = -80$ V.

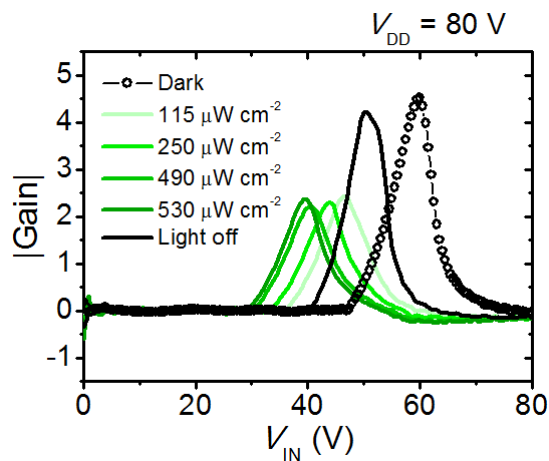


Figure S7. Voltage gain of the complementary inverter in dark and under green light with illumination intensities between 115-530 $\mu\text{W cm}^{-2}$.

Table S1. OFET performance of 6-BrIG film in the dark and under illumination.

	<i>n</i> -channel			<i>p</i> -channel		
	$\mu_{e,\text{max}}^a$ ($\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$)	$I_{\text{on}} / I_{\text{off}}$	V_{TH} (V)	$\mu_{h,\text{max}}$ ($\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$)	$I_{\text{on}} / I_{\text{off}}$	V_{TH} (V)
Dark	0.031 (0.030 ± 0.0004) ^b	$> 10^7$	43.6	5.8×10^{-4} (4.9 ± 0.8) $\times 10^{-4}$	$> 10^5$	-51.7
Mono chromic	0.034 (0.032 ± 0.0009)	$> 10^6$	35.8	7.6×10^{-4} (6.4 ± 0.5) $\times 10^{-4}$	$> 10^3$	-51.2
Poly chromic	0.032 (0.031 ± 0.0006)	$> 10^5$	33.8	8.7×10^{-4} (7.8 ± 0.6) $\times 10^{-4}$	$> 10^3$	-47.7

^a The maximum mobilities of the OFET devices ($L = 50 \mu\text{m}$ and $W/L = 17.5$). ^b The average mobilities and standard deviations are shown in parenthesis